

60 V, dual N-channel Trench MOSFET 12 May 2015

Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor			Ċ				
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C		-	-	330	mA
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	240	mA
Static characteristics (per transistor)							
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 200 mA; T _j = 25 °C		-	2.2	2.8	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1		
3	D2	drain TR2		$G1 \xrightarrow{f} G2$
4	S2	source TR2		
5	G2	gate TR2	TSSOP6 (SOT363)	
6	D1	drain TR1		S1 S2 017aaa256

6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
NX7002BKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363

7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
NX7002BKS	LT%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5.Limiting values

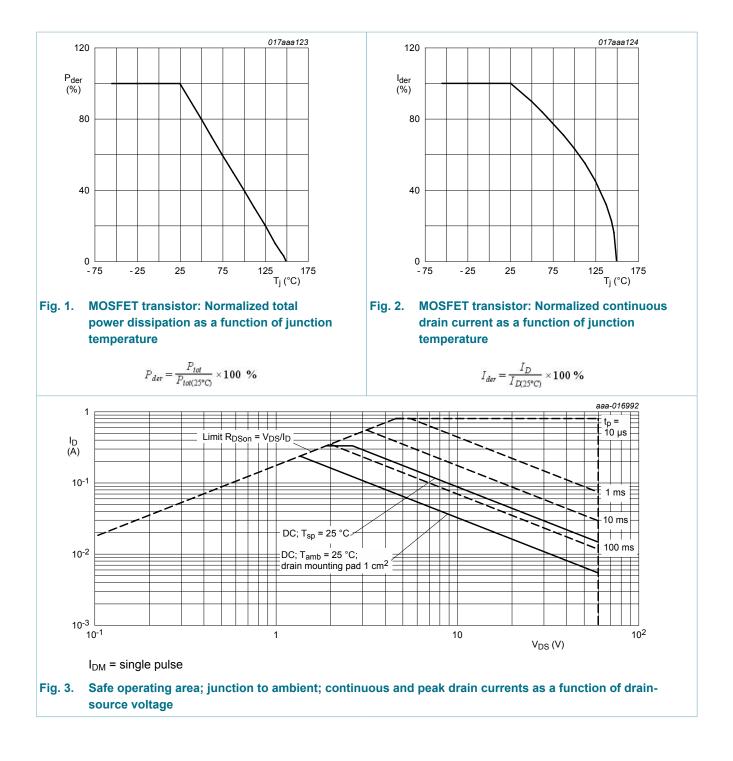
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor	· · · · · · · · · · · · · · · · · · ·				
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
ID	drain current	V _{GS} = 10 V; T _{sp} = 25 °C		-	330	mA
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	240	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	150	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	0.8	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	285	mW
			[1]	-	320	mW
		T _{sp} = 25 °C		-	870	mW
Source-dra	in diode			·		
I _S	source current	T _{amb} = 25 °C	[1]	-	200	mA
Per device						
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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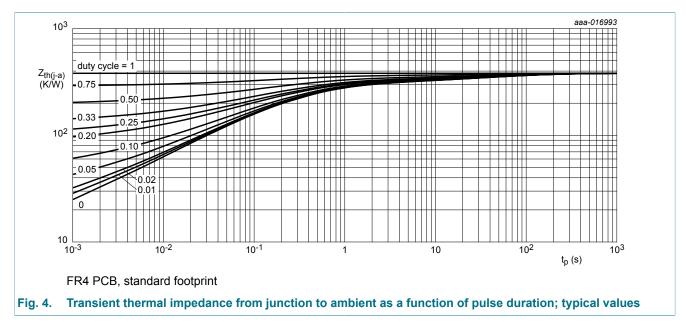


9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per transistor							
R _{th(j-a)}	thermal resistance	in free air	[1]	-	380	440	K/W
	from junction to ambient		[2]	-	340	390	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	125	145	K/W

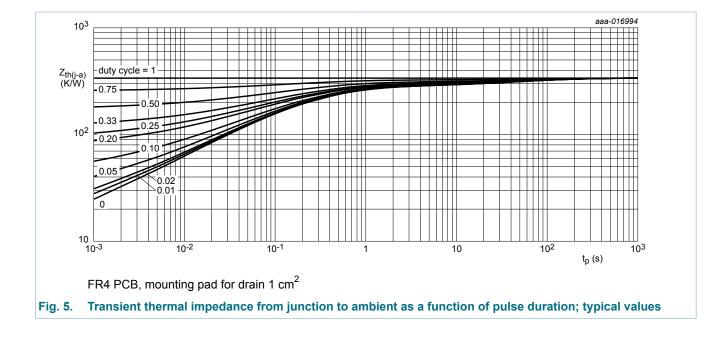
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



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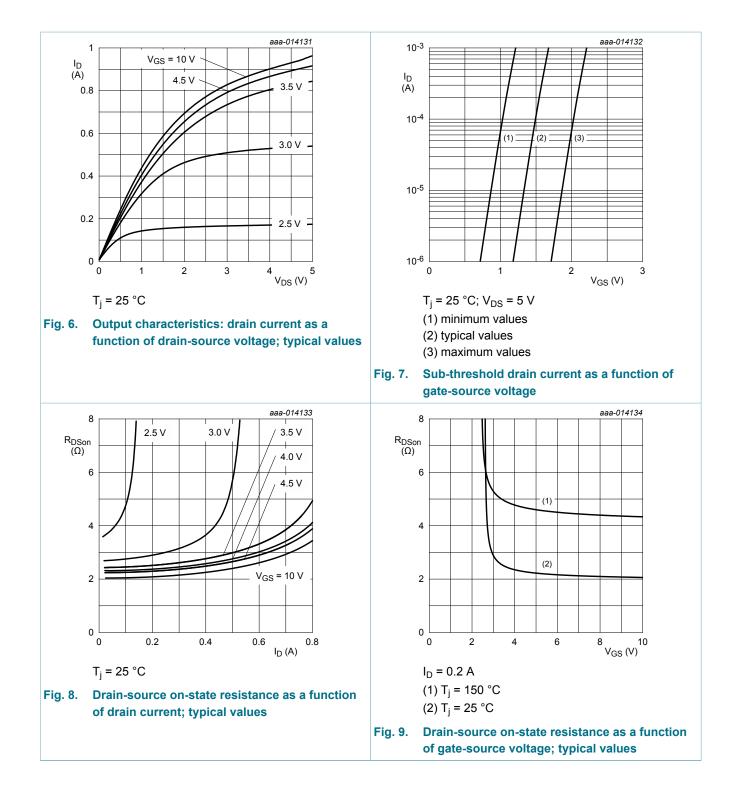
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics (per transistor)	-				
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V_{GS} = 5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.3	μA
		V_{GS} = -5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-0.3	μA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 200 mA; T _j = 25 °C	-	2.2	2.8	Ω
re	resistance	V_{GS} = 10 V; I _D = 200 mA; T _j = 150 °C	-	4.5	5.7	Ω
		V _{GS} = 5 V; I _D = 200 mA; T _j = 25 °C	-	2.5	3.2	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I _D = 200 mA; T _j = 25 °C	-	600	-	mS
R _G	gate resistance	f = 1 MHz	-	2.5	-	Ω
Dynamic c	haracteristics (per transist	or)				
Q _{G(tot)}	total gate charge	V_{DS} = 30 V; I _D = 200 mA; V _{GS} = 10 V;	-	1	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q _{GD}	gate-drain charge	-	-	0.18	-	nC
C _{iss}	input capacitance	V_{DS} = 10 V; f = 1 MHz; V_{GS} = 0 V;	-	23.6	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4.6	-	pF
C _{rss}	reverse transfer capacitance	-	-	3	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 50 V; I _D = 200 mA; V _{GS} = 10 V;	-	4.7	-	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	4.3	-	ns
t _{d(off)}	turn-off delay time	1	-	6.9	-	ns
t _f	fall time		-	2.9	-	ns
Source-dra	in diode (per transistor)	1	II		1	
V _{SD}	source-drain voltage	I _S = 50 mA; V _{GS} = 0 V; T _i = 25 °C	-	0.87	1.2	V

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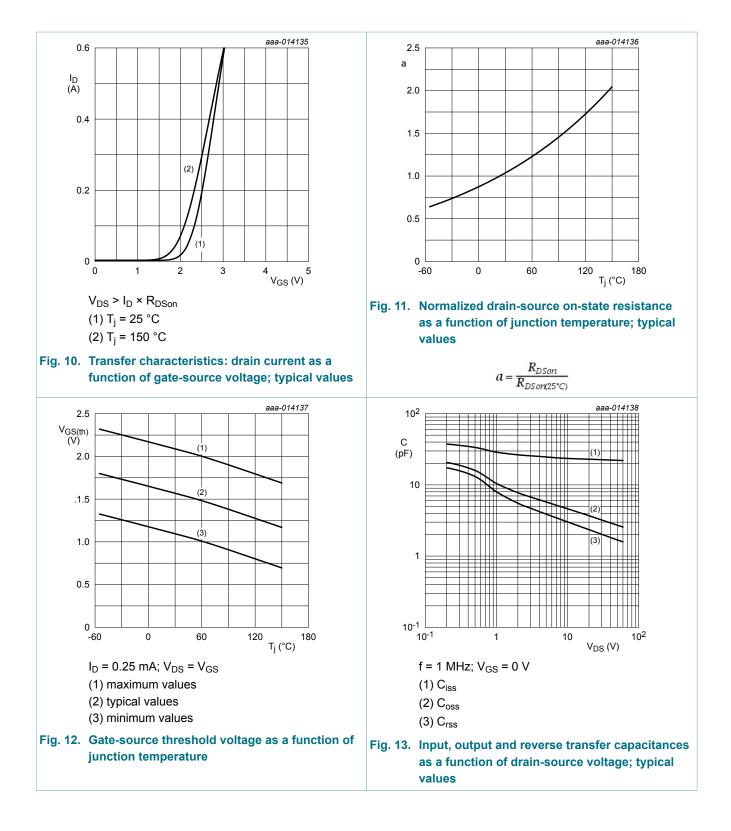


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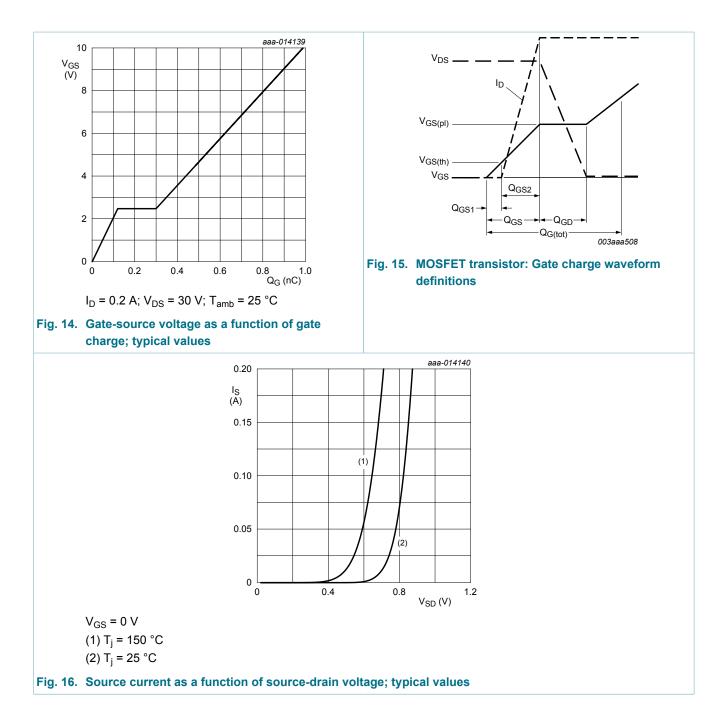


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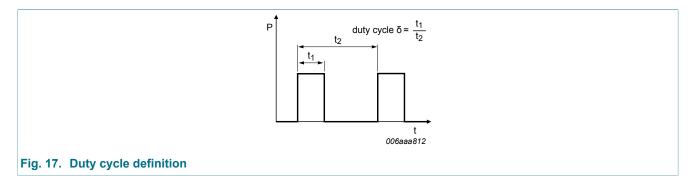
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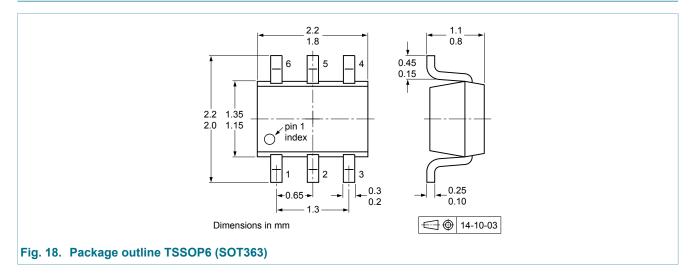


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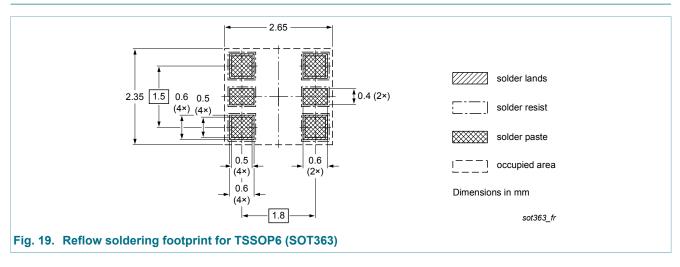
11. Test information



12. Package outline



13. Soldering

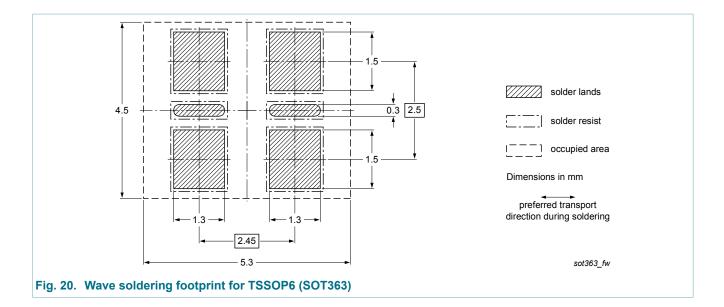


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14. Revision history

Table 8. Revision his	. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
NX7002BKS v.1	20150512	Product data sheet	-	-			

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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